

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.2	—	V/°C	$V_{GE} = 0V, I_C = 1mA$ (25°C-150°C) ③
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 30A, V_{GE} = 15V, T_J = 25^\circ\text{C}$ ②
		—	2.1	—		$I_C = 30A, V_{GE} = 15V, T_J = 150^\circ\text{C}$ ②
		—	2.2	—		$I_C = 30A, V_{GE} = 15V, T_J = 175^\circ\text{C}$ ②
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0	V	$V_{CE} = V_{GE}, I_C = 1mA$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-16	—	mV/°C	$V_{CE} = V_{GE}, I_C = 1mA$ (25°C - 175°C)
g_{fe}	Forward Transconductance	—	32	—	S	$V_{CE} = 50V, I_C = 30A, PW = 80\mu s$
I_{CES}	Collector-to-Emitter Leakage Current	—	1	150	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	700	—		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	157	236	nC	$I_C = 30A$ ② $V_{GE} = 15V$ $V_{CC} = 600V$
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	21	32		
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	69	104		
E_{on}	Turn-On Switching Loss	—	2105	2374	μJ	$I_C = 30A, V_{CC} = 600V, V_{GE} = 15V$ ② $R_G = 10\Omega, L = 200\mu H, T_J = 25^\circ\text{C}$ Energy losses include tail & diode reverse recovery Diode clamp the same as IRG7PH42UDPbF
E_{off}	Turn-Off Switching Loss	—	1182	1424		
E_{total}	Total Switching Loss	—	3287	3798		
$t_{d(on)}$	Turn-On delay time	—	25	34	ns	Diode clamp the same as IRG7PH42UDPbF
t_r	Rise time	—	32	41		
$t_{d(off)}$	Turn-Off delay time	—	229	271		
t_f	Fall time	—	63	86		
E_{on}	Turn-On Switching Loss	—	3186	—	μJ	$I_C = 30A, V_{CC} = 600V, V_{GE} = 15V$ ② $R_G = 10\Omega, L = 200\mu H, T_J = 175^\circ\text{C}$ Energy losses include tail & diode reverse recovery Diode clamp the same as IRG7PH42UDPbF
E_{off}	Turn-Off Switching Loss	—	2153	—		
E_{total}	Total Switching Loss	—	5339	—		
$t_{d(on)}$	Turn-On delay time	—	20	—	ns	Diode clamp the same as IRG7PH42UDPbF
t_r	Rise time	—	31	—		
$t_{d(off)}$	Turn-Off delay time	—	310	—		
t_f	Fall time	—	162	—		
C_{ies}	Input Capacitance	—	3338	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$
C_{oes}	Output Capacitance	—	124	—		
C_{res}	Reverse Transfer Capacitance	—	75	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$I_C = 120A$ $V_{CC} = 960V, V_p = 1200V$ $R_g = 10\Omega, V_{GE} = +20V$ to $0V, T_J = 175^\circ\text{C}$

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 22\mu H, R_G = 10\Omega$
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 78A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.

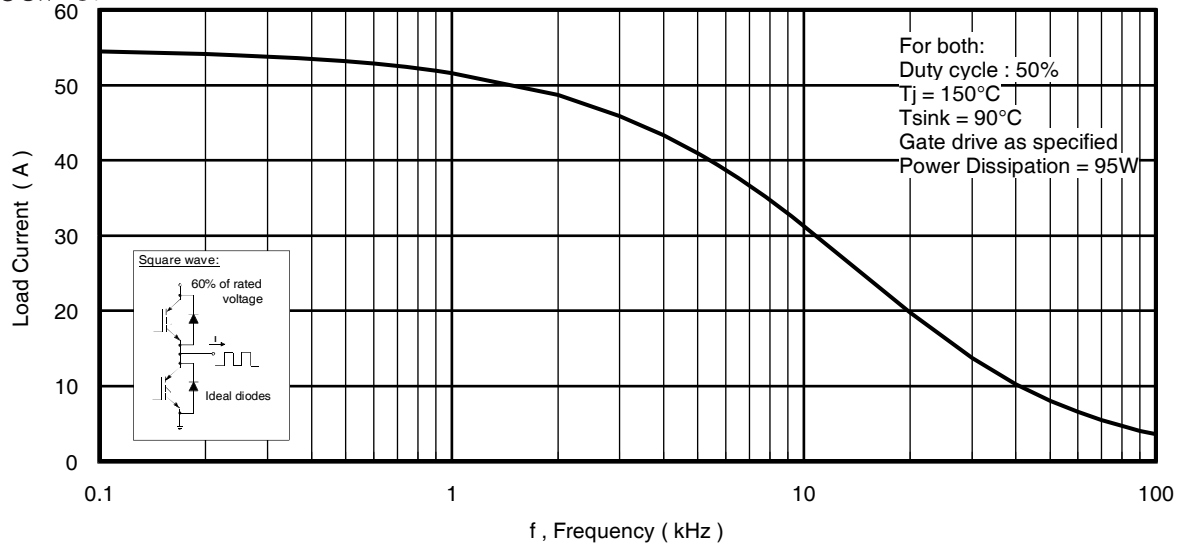


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

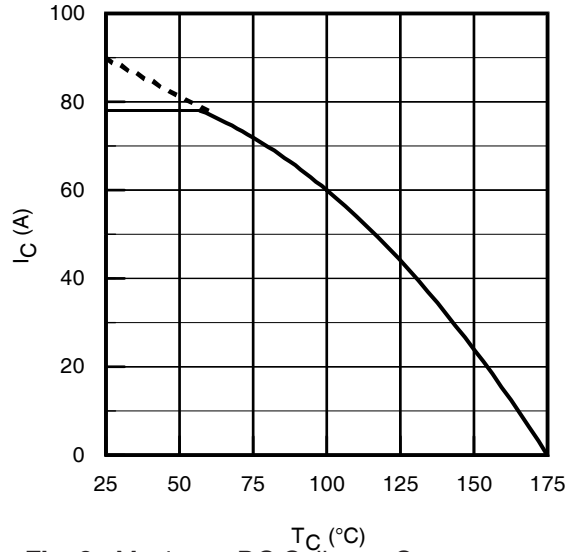


Fig. 2 - Maximum DC Collector Current vs. Case Temperature

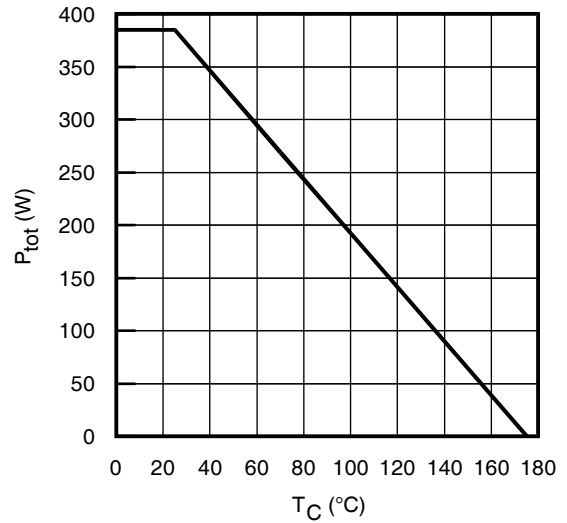


Fig. 3 - Power Dissipation vs. Case Temperature

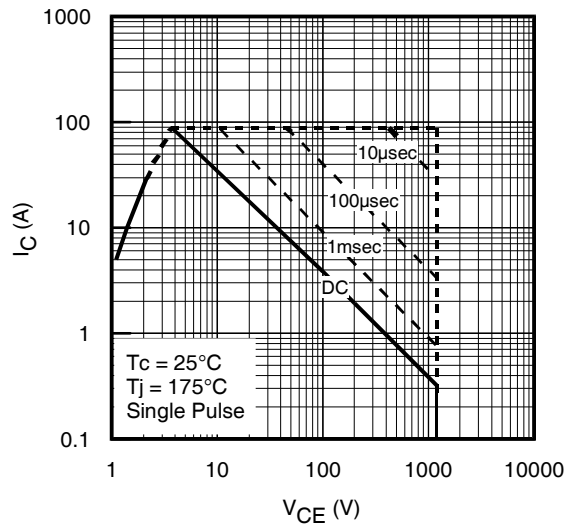


Fig. 4 - Forward SOA
 $T_C = 25^{\circ}\text{C}$, $T_J \leq 175^{\circ}\text{C}$; $V_{GE} = 15\text{V}$

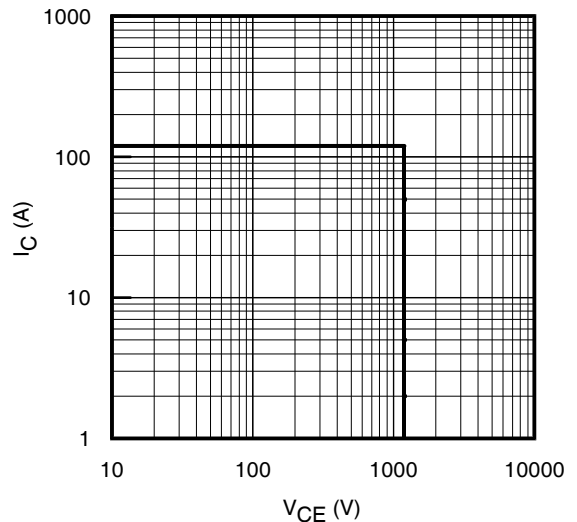


Fig. 5 - Reverse Bias SOA
 $T_J = 175^{\circ}\text{C}$; $V_{GE} = 20\text{V}$

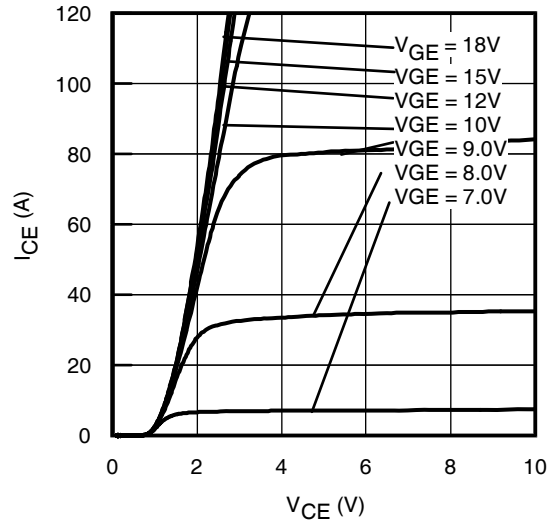


Fig. 6 - Typ. IGBT Output Characteristics
T_J = -40°C; t_p = 20μs

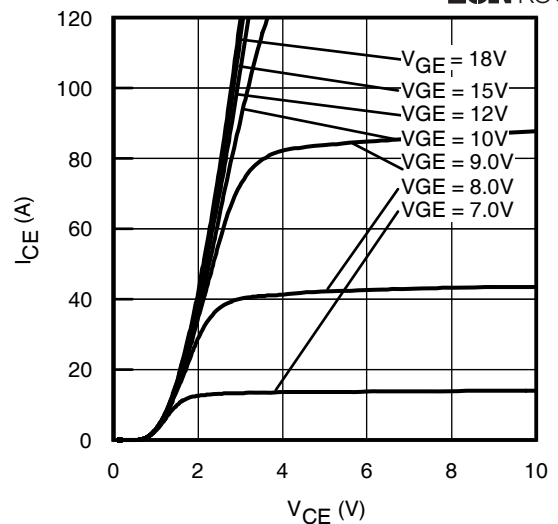


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 25°C; t_p = 20μs

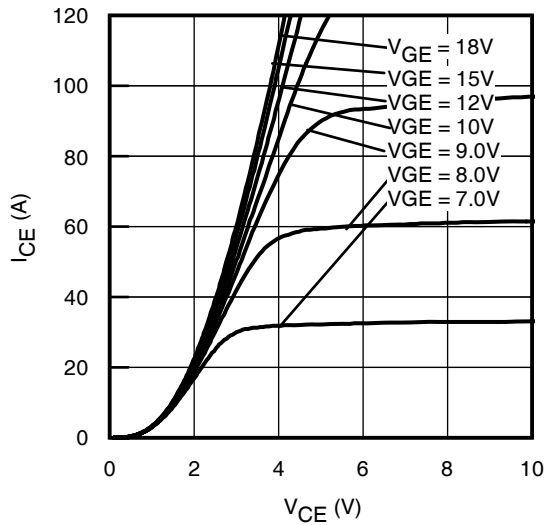


Fig. 8 - Typ. IGBT Output Characteristics
T_J = 175°C; t_p = 20μs

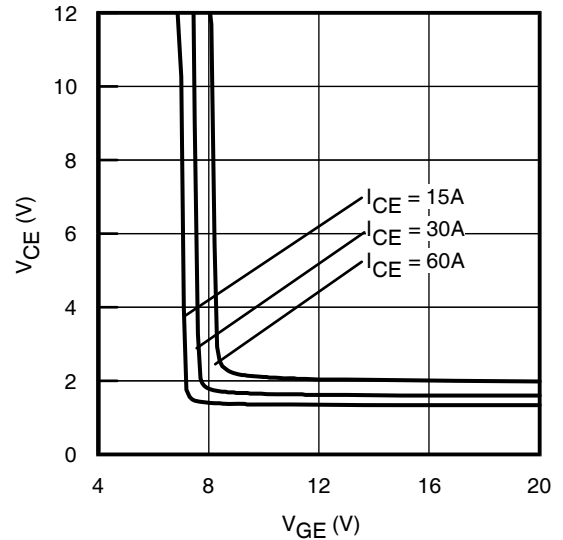


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

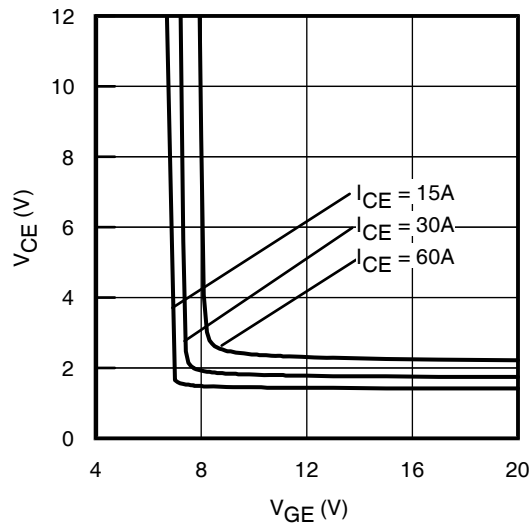


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

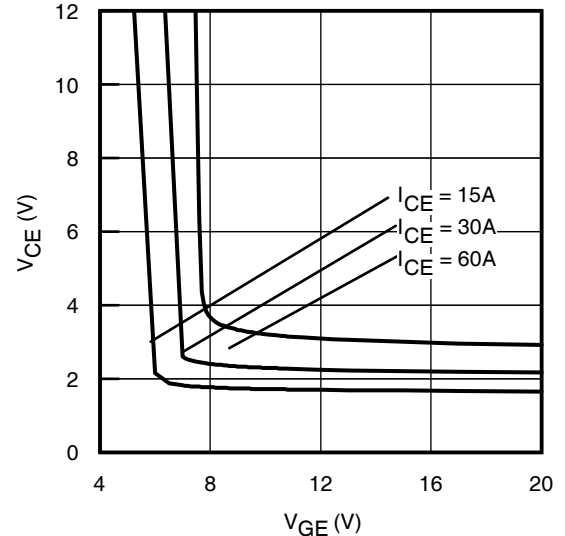


Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 175°C

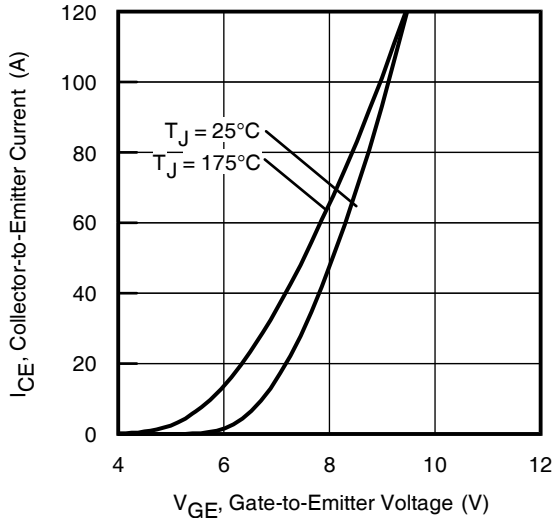


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 20\mu\text{s}$

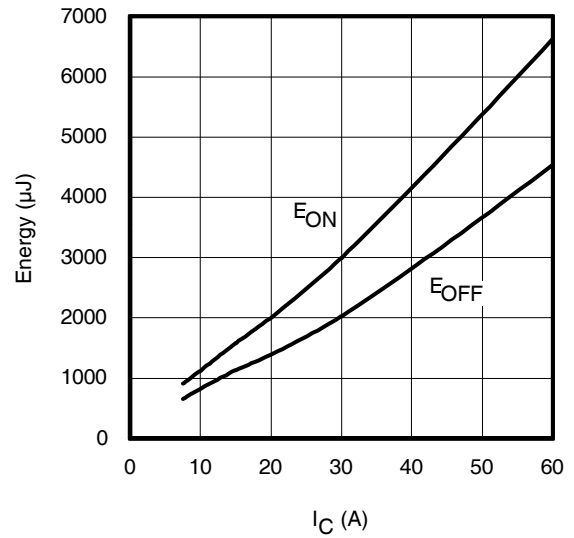


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

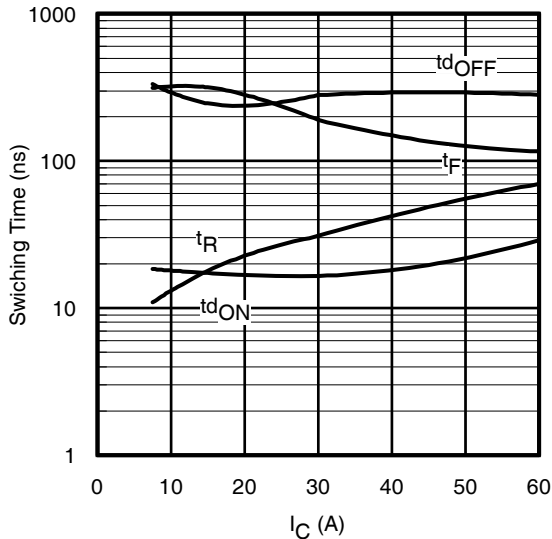


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

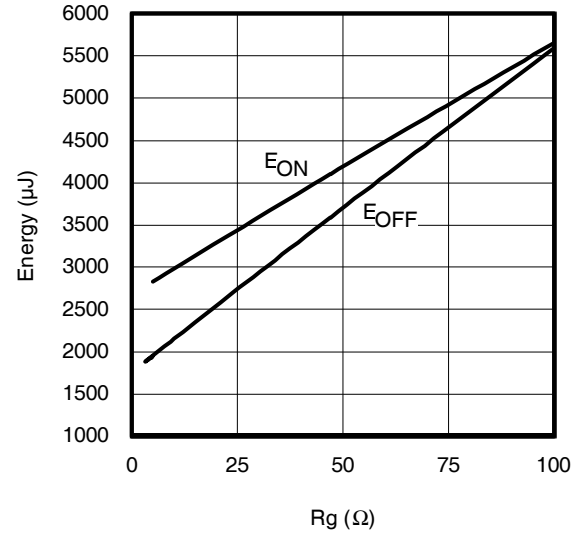


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $I_{CE} = 30\text{A}$; $V_{GE} = 15\text{V}$

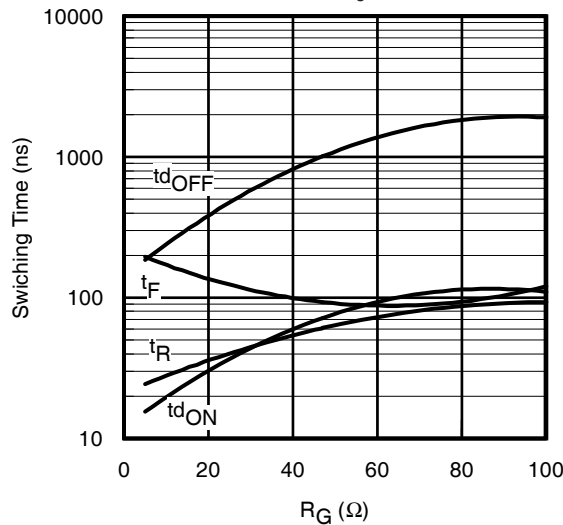


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $I_{CE} = 30\text{A}$; $V_{GE} = 15\text{V}$

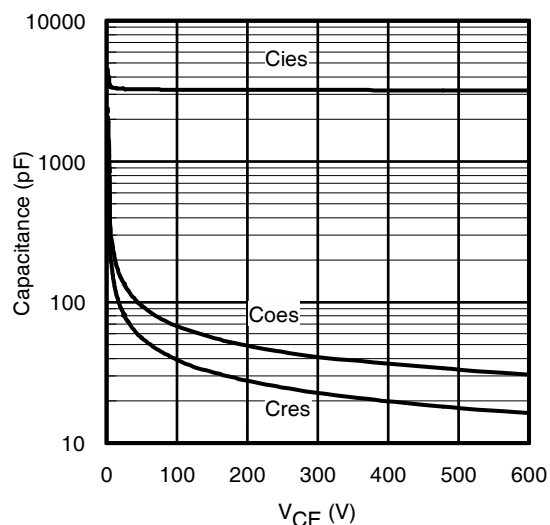


Fig. 17 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

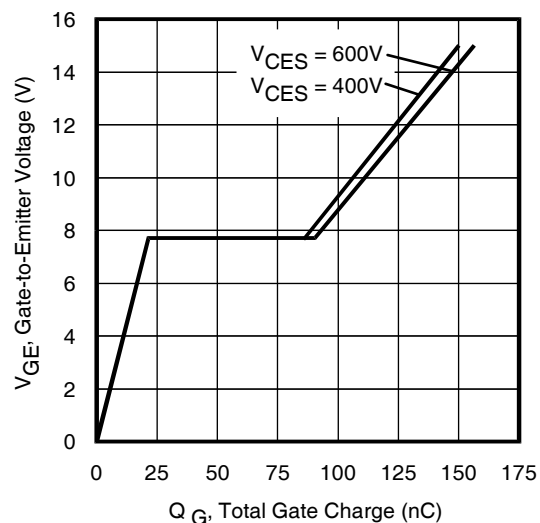


Fig. 18- Typical Gate Charge vs. V_{GE}
 $I_{CE} = 30A$; $L = 600\mu H$

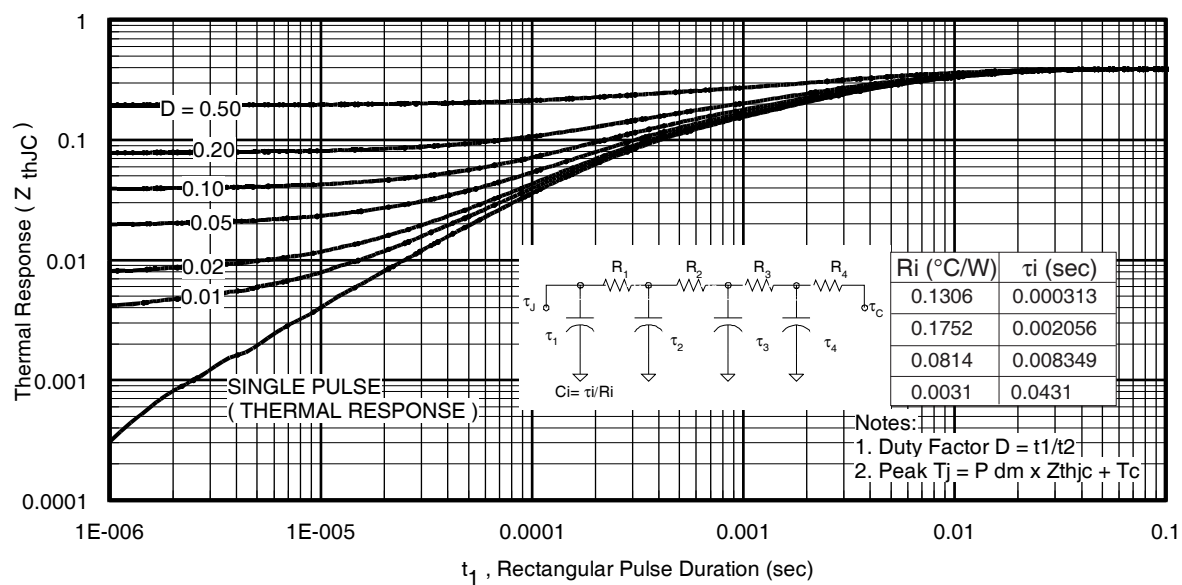


Fig 19. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT) TO-247AC

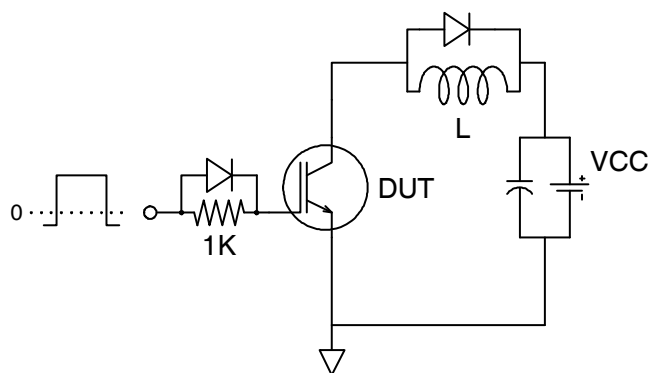


Fig.C.T.1 - Gate Charge Circuit (turn-off)

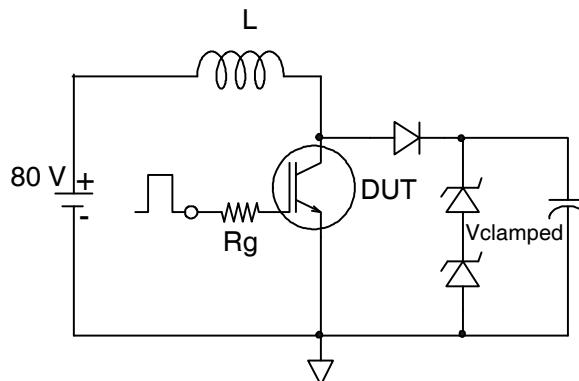


Fig.C.T.2 - RBSOA Circuit

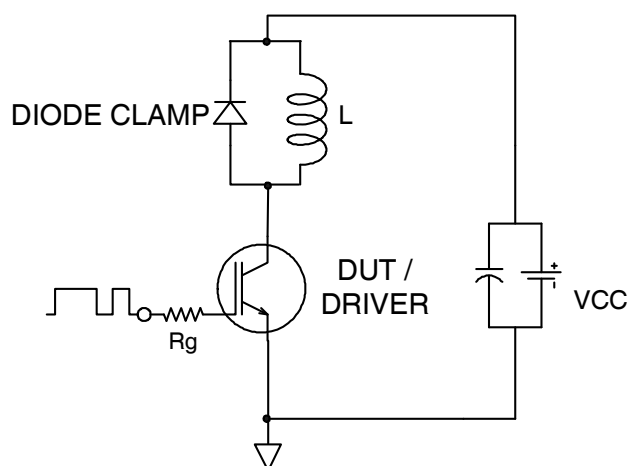


Fig.C.T.3 - Switching Loss Circuit

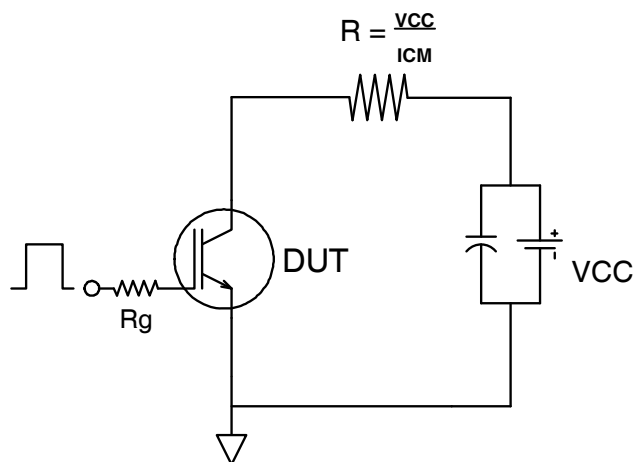


Fig.C.T.4 - Resistive Load Circuit

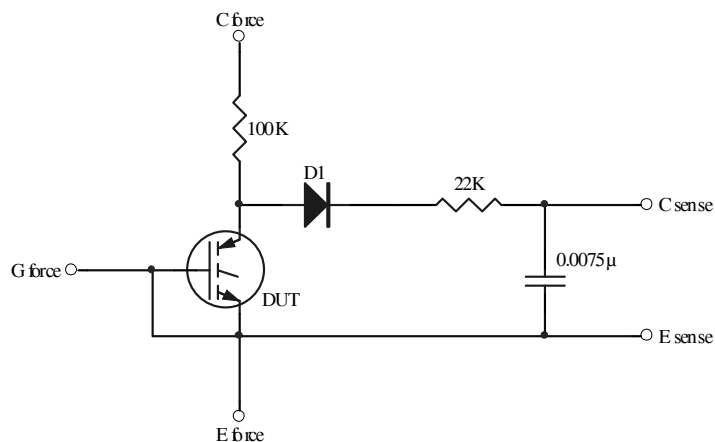


Fig.C.T.5 - BVCES Filter Circuit

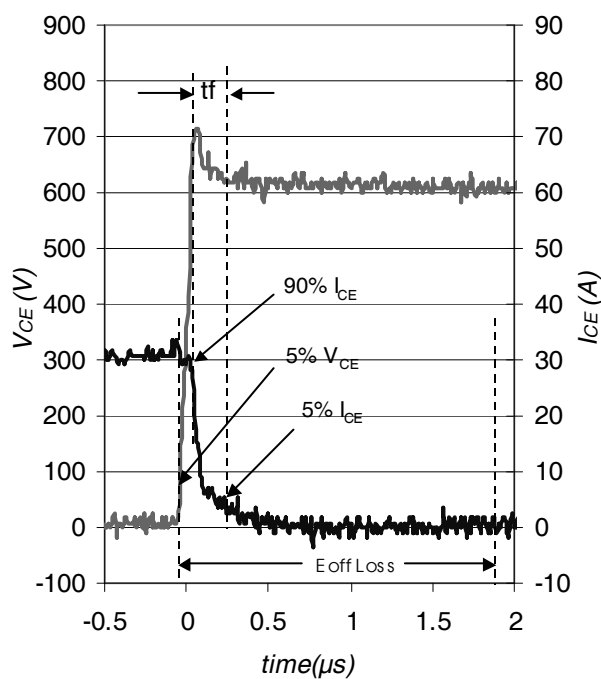


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

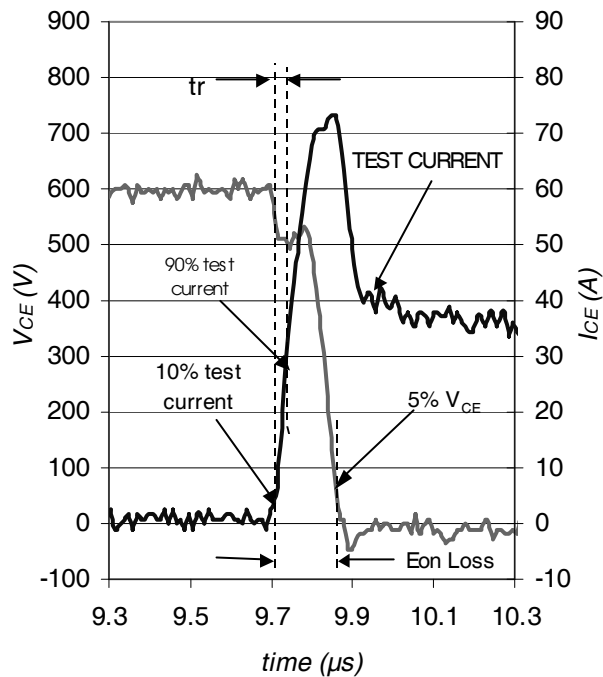
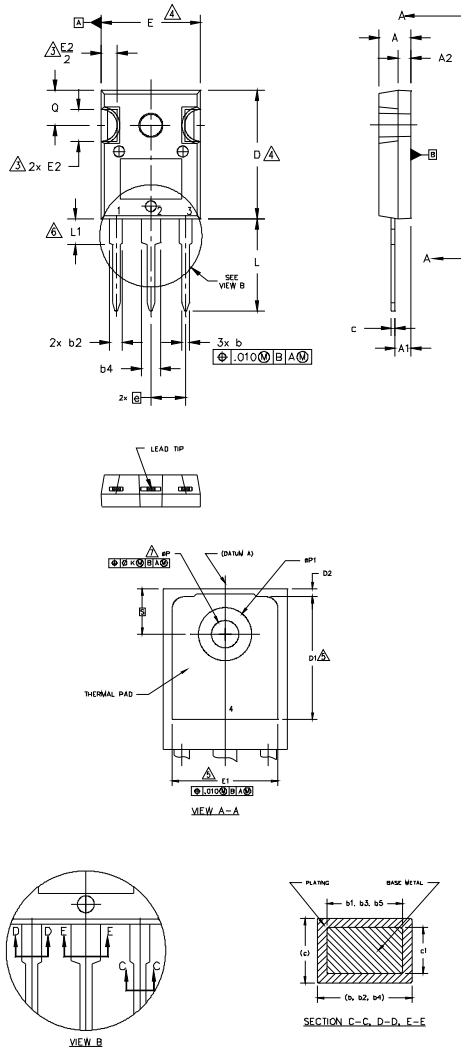


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
 2. DIMENSIONS ARE SHOWN IN INCHES.
 3. CONTOUR OF SLOT OPTIONAL.
 4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
 6. LEAD FINISH UNCONTROLLED IN L1.
 7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
- B. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

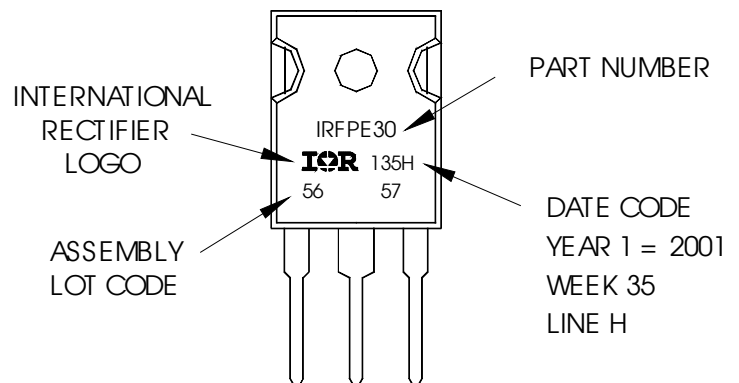
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"

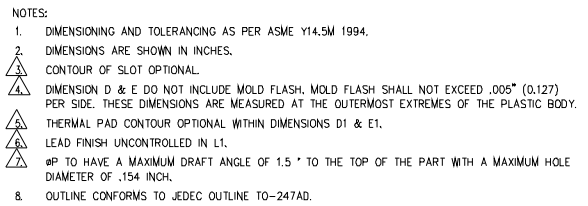


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



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	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.130	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.780	.827	19.71	21.00	
L1	.146	.169	3.71	4.29	
oP	.140	.144	3.56	3.66	
eP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

Diagram illustrating the markings on a MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo.
- ASSEMBLY LOT CODE**: Points to the code 56.
- PART NUMBER**: Points to the code IRGP30B120KD-E.
- DATE CODE**: Points to the code 035H.
- YEAR 0 = 2000**: Explanation of the date code.
- WEEK 35**: Explanation of the date code.
- LINE H**: Explanation of the date code.

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